

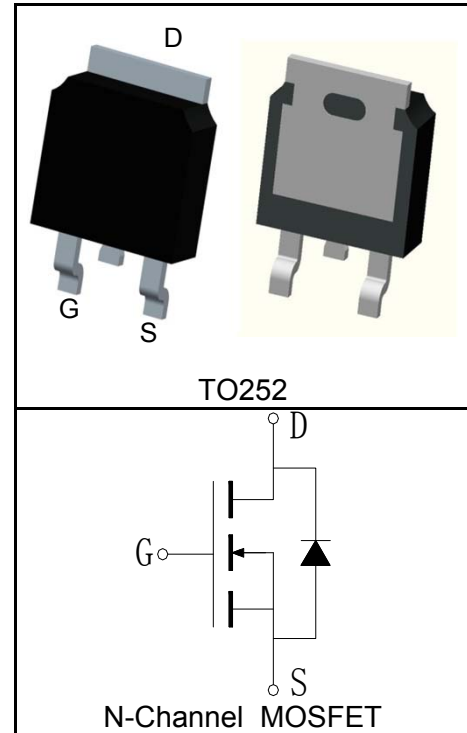
Features

- 30V/75A,
 $R_{DS(ON)} = 4.5m\Omega(Typ.)@V_{GS}=10V$
 $R_{DS(ON)} = 7m\Omega(Typ.)@V_{GS}=4.5V$
- Super High Dense Cell Design
- Ultra Low On-Resistance
- 100% avalanche tested
- Lead Free and Green Devices Available (RoHS Compliant)

Applications

- Load Switch

Pin Description



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C=25^\circ C$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	30	V
V_{GSS}	Gate-Source Voltage	± 20	
T_J	Maximum Junction Temperature	175	$^\circ C$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ C$
I_S	Diode Continuous Forward Current	$T_C=25^\circ C$ 75	A
Mounted on Large Heat Sink			
$I_{DP}^{①}$	300 μs Pulse Drain Current Tested	$T_C=25^\circ C$ 300	A
$I_D^{②}$	Continuous Drain Current($V_{GS}=10V$)	$T_C=25^\circ C$ 75	A
		$T_C=100^\circ C$ 52	
P_D	Maximum Power Dissipation	$T_C=25^\circ C$ 50	W
		$T_C=100^\circ C$ 25	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	3	$^\circ C/W$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	100	$^\circ C/W$
Drain-Source Avalanche Ratings			
$E_{AS}^{③}$	Avalanche Energy, Single Pulsed	90	mJ

Electrical Characteristics ($T_C=25^\circ\text{C}$ Unless Otherwise Noted)

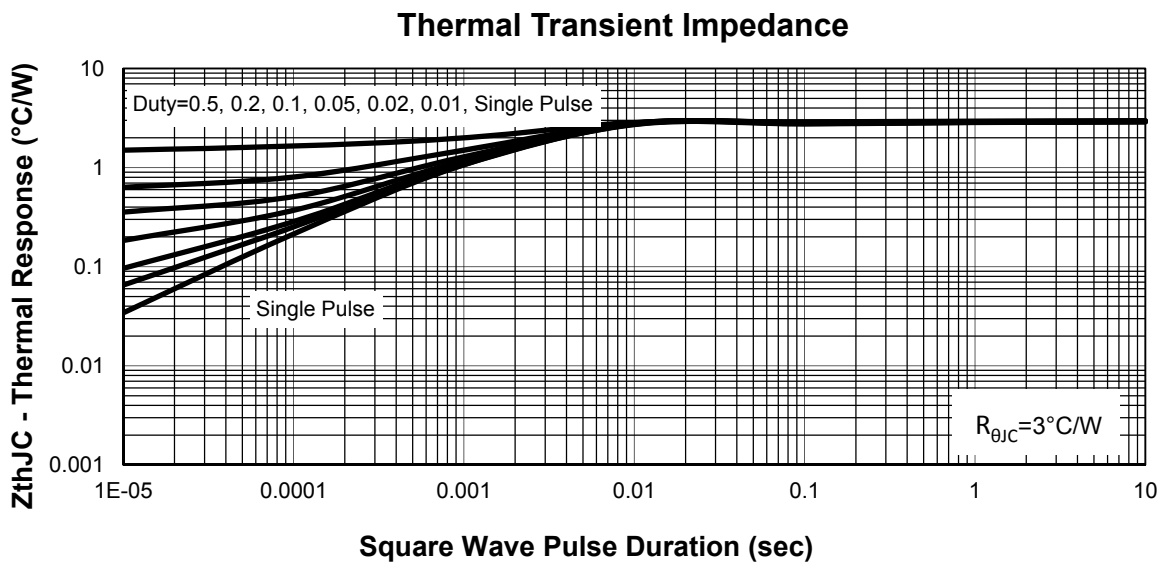
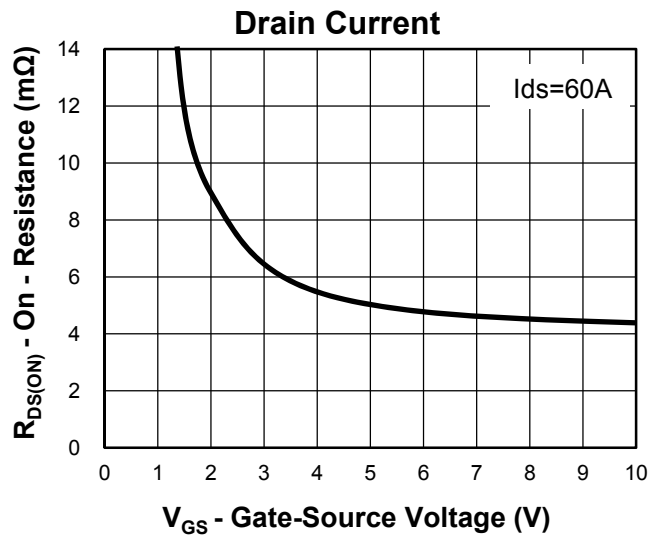
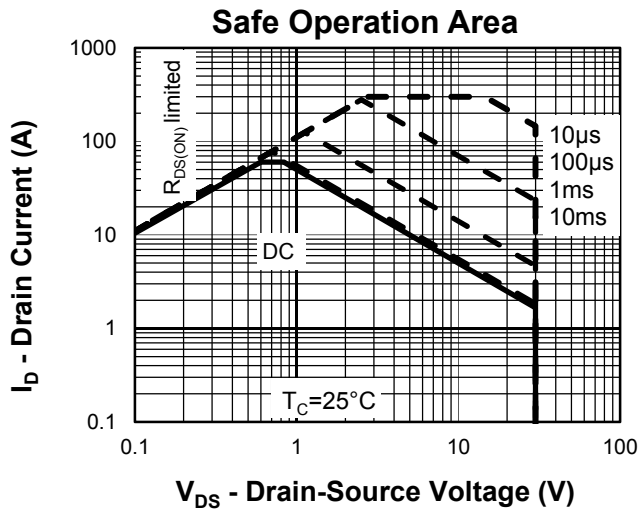
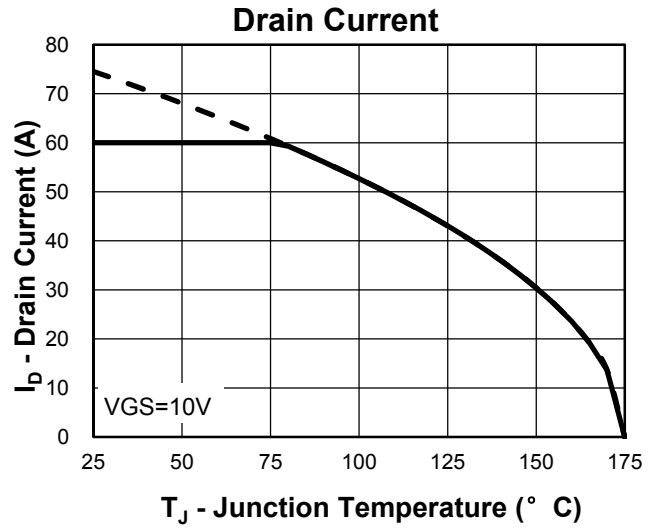
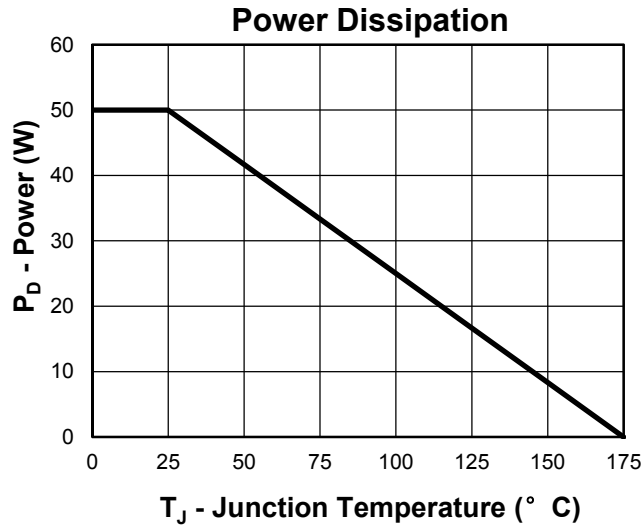
Symbol	Parameter	Test Condition	RU3075L			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_{DS}=250\mu A$	30			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{DS}=30V, V_{GS}=0V$			1	μA
		$T_J=125^\circ C$			30	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{DS}=V_{GS}, I_{DS}=250\mu A$	1		3	V
I_{GSS}	Gate Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$			± 100	nA
$R_{DS(ON)}^{(4)}$	Drain-Source On-state Resistance	$V_{GS}=10V, I_{DS}=60A$		4.5	6	$m\Omega$
		$V_{GS}=4.5V, I_{DS}=45A$		7	9	$m\Omega$
Diode Characteristics						
$V_{SD}^{(4)}$	Diode Forward Voltage	$I_{SD}=60A, V_{GS}=0V$			1.2	V
t_{rr}	Reverse Recovery Time	$I_{SD}=60A, di_{SD}/dt=100A/\mu s$		27		ns
Q_{rr}	Reverse Recovery Charge			16		nC
Dynamic Characteristics ⁽⁵⁾						
R_G	Gate Resistance	$V_{GS}=0V, V_{DS}=0V, F=1MHz$		1.5		Ω
C_{iss}	Input Capacitance	$V_{GS}=0V,$ $V_{DS}=15V,$ Frequency=1.0MHz		2450		pF
C_{oss}	Output Capacitance			490		
C_{rss}	Reverse Transfer Capacitance			240		
$t_{d(ON)}$	Turn-on Delay Time	$V_{DD}=15V, I_{DS}=60A,$ $V_{GEN}=10V, R_G=5\Omega$		15		ns
t_r	Turn-on Rise Time			68		
$t_{d(OFF)}$	Turn-off Delay Time			36		
t_f	Turn-off Fall Time			29		
Gate Charge Characteristics ⁽⁵⁾						
Q_g	Total Gate Charge	$V_{DS}=24V, V_{GS}=10V,$ $I_{DS}=60A$		42		nC
Q_{gs}	Gate-Source Charge			10		
Q_{gd}	Gate-Drain Charge			13		

- Notes:**
- ①Pulse width limited by safe operating area.
 - ②Calculated continuous current based on maximum allowable junction temperature. The package limitation current is 60A.
 - ③Limited by T_{Jmax} , $I_{AS}=19A$, $V_{DD}=48V$, $R_G=50\Omega$, Starting $T_J=25^\circ C$.
 - ④Pulse test; Pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.
 - ⑤Guaranteed by design, not subject to production testing.

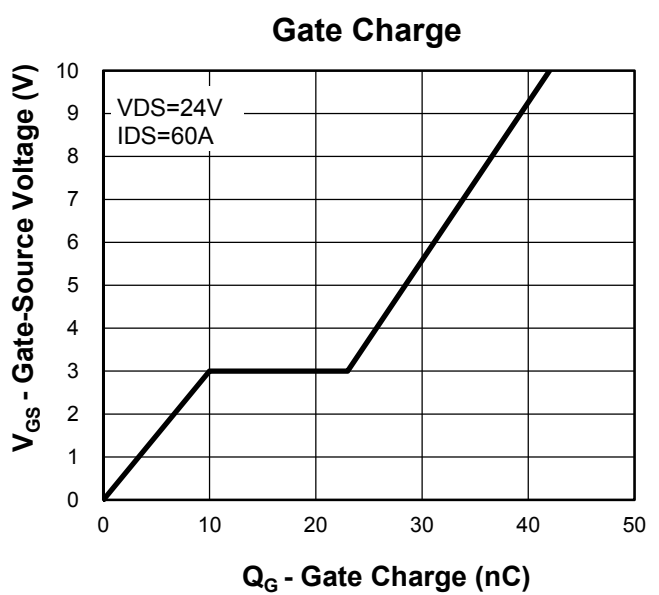
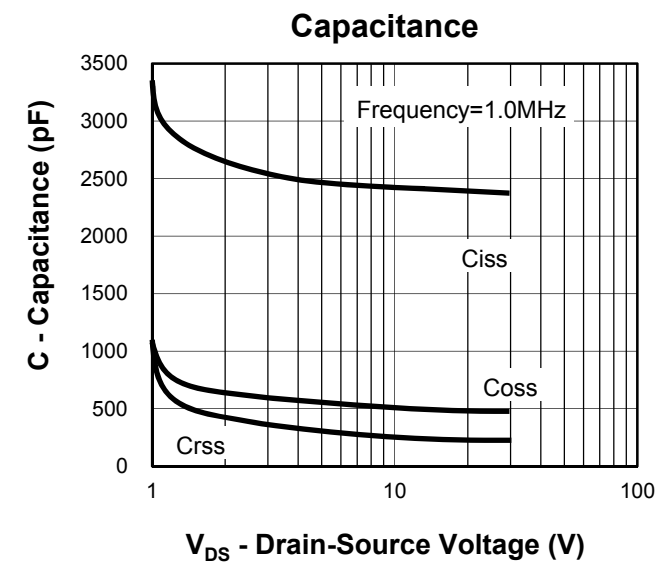
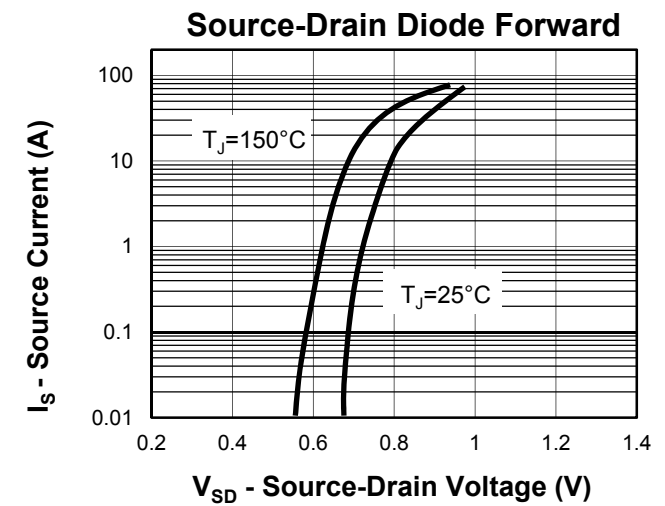
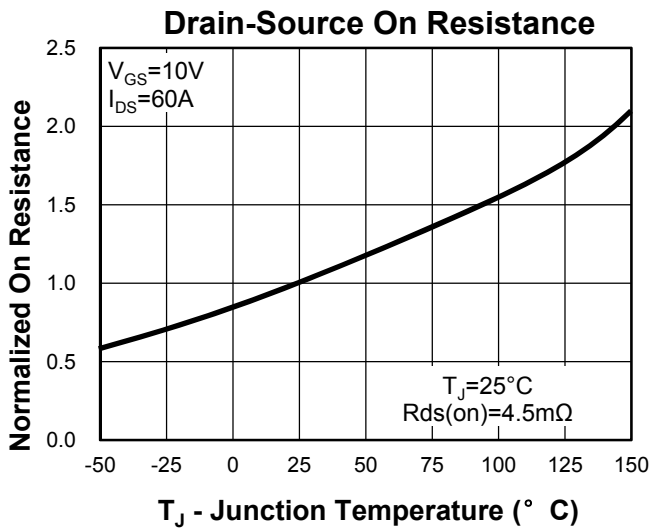
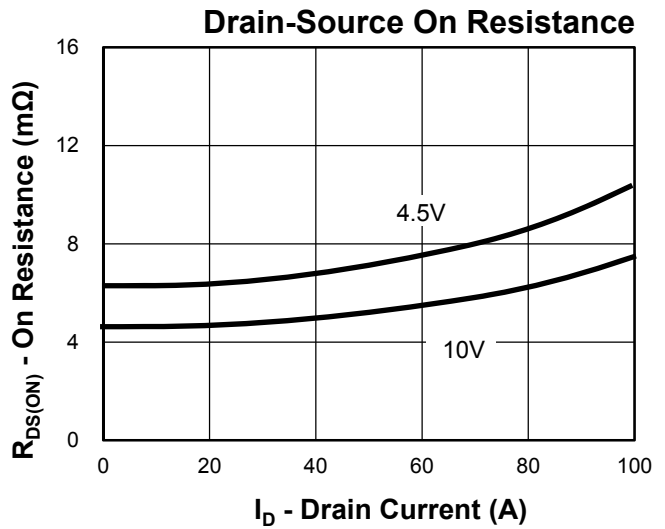
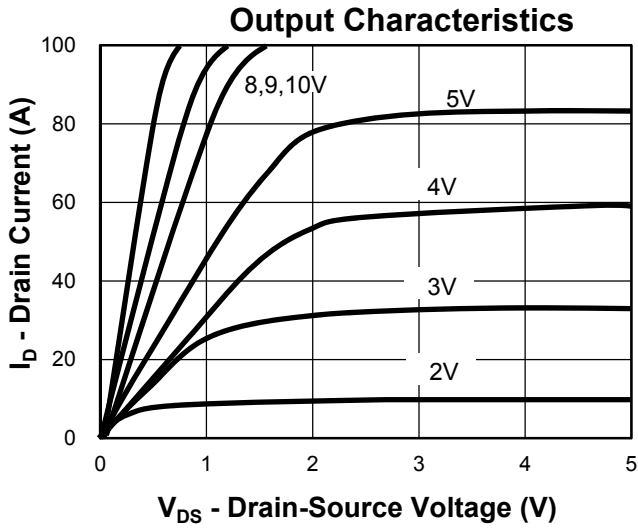
Ordering and Marking Information

Device	Marking	Package	Packaging	Quantity	Reel Size	Tape width
RU3075L	RU3075L	TO252	Tape&Reel	2500	13"	16mm

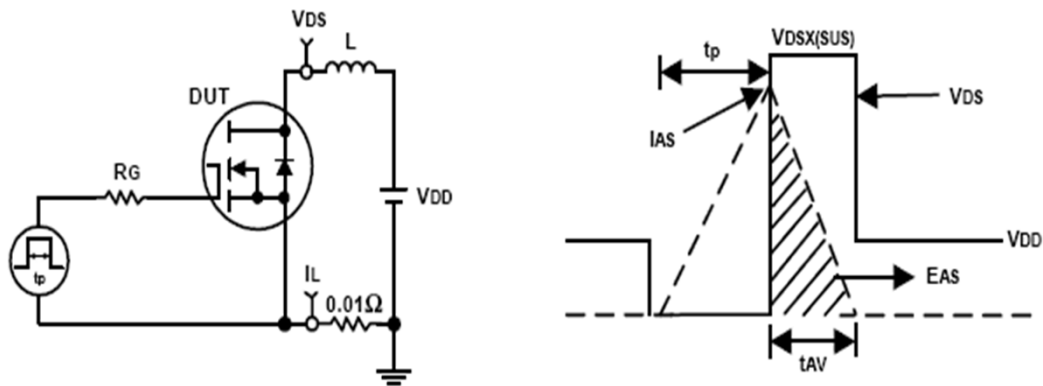
Typical Characteristics



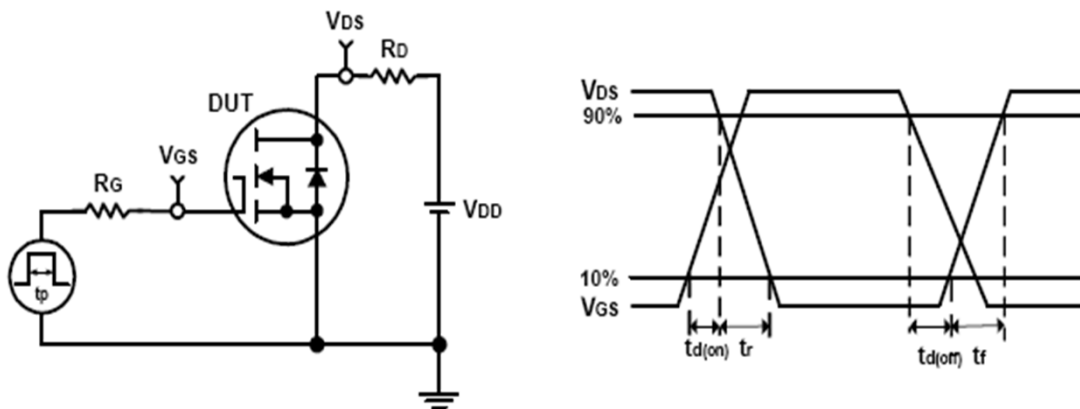
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Avalanche Test Circuit and Waveforms

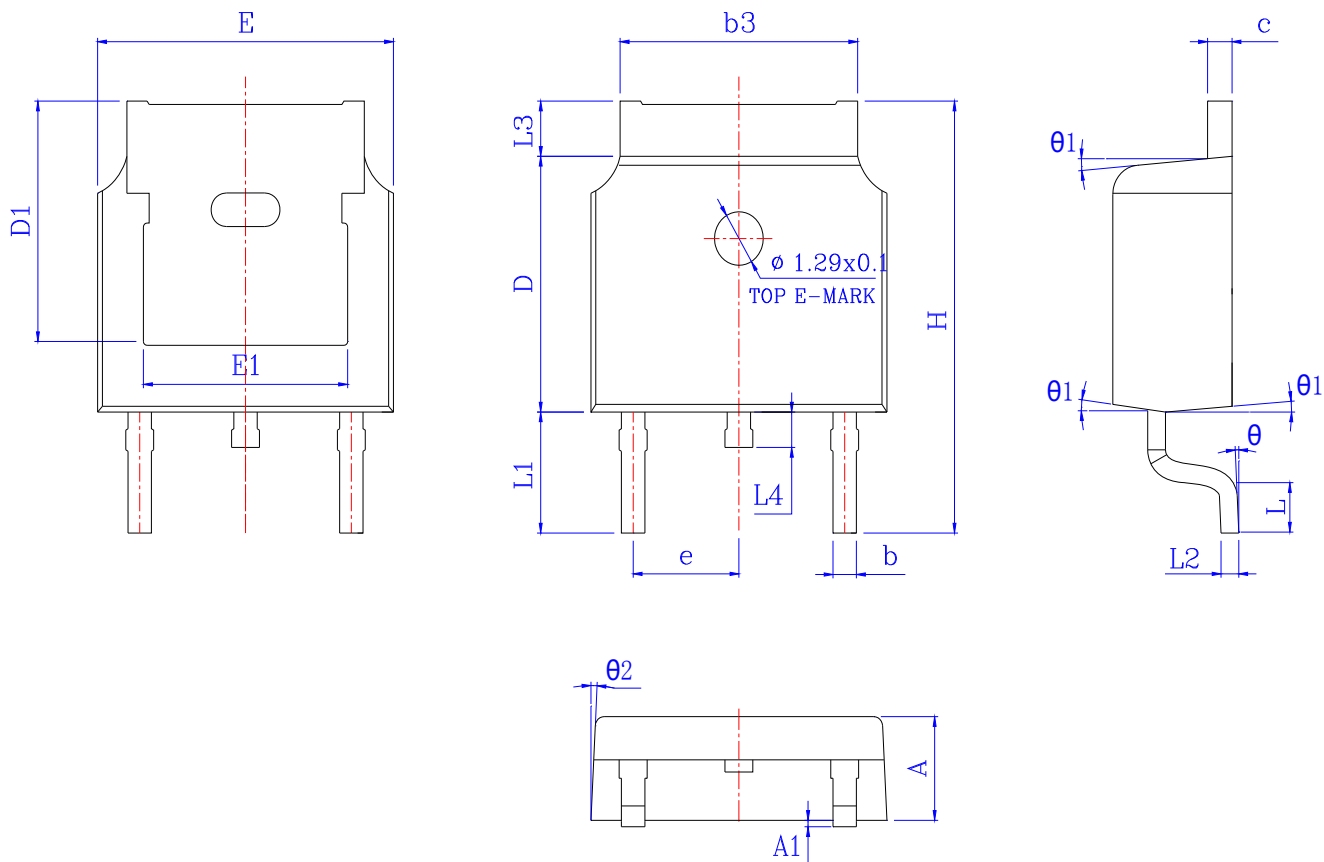


Switching Time Test Circuit and Waveforms



Package Information

TO252



SYMBOL	MM			INCH		
	MIN	NOM	MAX	MIN	NOM	MAX
A	2.200	2.300	2.400	0.087	0.091	0.094
A1	*	*	0.100	*	*	0.004
b	0.660	0.760	0.860	0.026	0.030	0.034
b3	5.130	5.295	5.460	0.202	0.208	0.215
c	0.470	0.535	0.600	0.019	0.021	0.024
D	6.000	6.100	6.200	0.236	0.240	0.244
D1	5.30 REF			0.20 REF		
E	6.500	6.600	6.700	0.256	0.260	0.264
E1	4.700	4.810	4.920	0.185	0.189	0.194
e	2.28 REF			0.09 REF		
H	9.800	10.100	10.400	0.386	0.398	0.409
L	1.400	1.550	1.700	0.055	0.061	0.067
L1	2.743 REF			0.108 REF		
L2	0.510 BSC			0.020 BSC		
L3	0.900	1.075	1.250	0.035	0.042	0.049
L4	0.600	0.800	1.000	0.024	0.031	0.039
θ	0°	*	8°	0°	*	8°
θ_1	5°	7°	9°	5°	7°	9°
θ_2	5°	7°	9°	5°	7°	9°

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